

Schottky barrier diode

RB521S-30

New

●Applications

Low current rectification and high speed switching

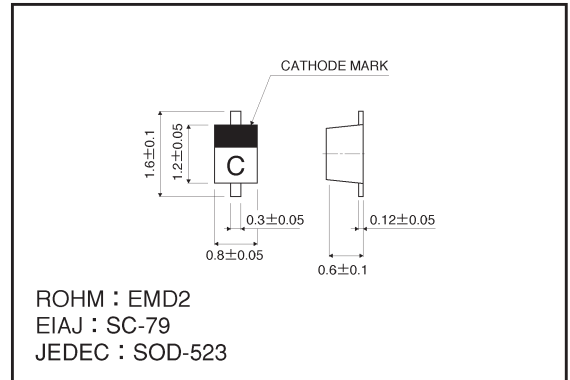
●Features

- 1) Small surface mounting type.(EMD2)
- 2) High rectifying current of 200 mA with the small package.
- 3) Low reverse current and low forward voltage.

●Construction

Silicon epitaxial planar

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	30	V
Mean rectifying current	I_o	200	mA
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	0.40	0.50	V	$I_F=200\text{mA}$
Reverse current	I_R	—	4.0	30	μA	$V_R=10\text{V}$

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

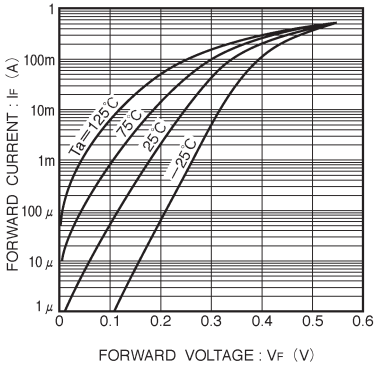


Fig. 1 Forward characteristics

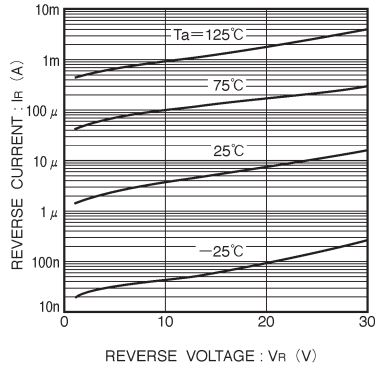


Fig. 2 Reverse characteristics

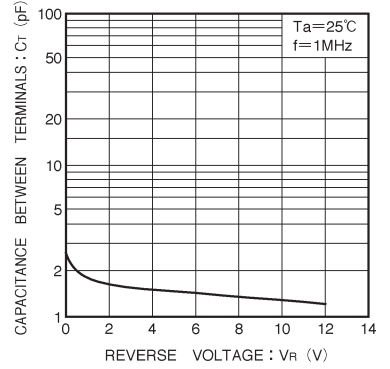


Fig. 3 Capacitance between terminals characteristics

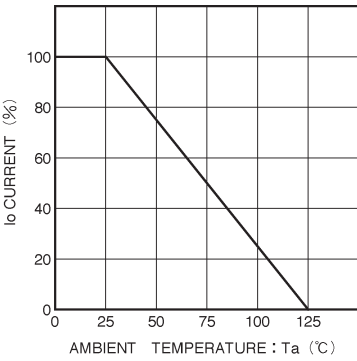


Fig. 4 Derating curve
(mounting on glass epoxy PCBs)